

Switching (250V, 5A)

2SK2460N

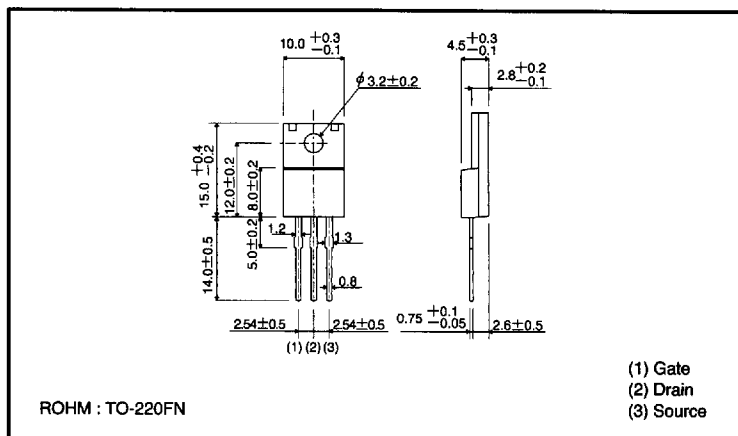
●Features

- 1) Low on-resistance.
- 2) High-speed switching.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage guaranteed at $V_{GS} = \pm 30V$.
- 5) Easily designed drive circuits.
- 6) Easy to use in parallel.

●Structure

Silicon N-channel
MOSFET transistor

●External dimensions (Units: mm)



●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DS}	250	V
Gate-source voltage		V_{GS}	± 30	V
Drain current	Continuous	I_D	5	A
	Pulsed	I_{DP}^*	20	A
Drain reverse current	Continuous	I_{DR}	5	A
	Pulsed	I_{DRP}^*	20	A
Total power dissipation ($T_c=25^\circ C$)		P_D	30	W
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature		T_{stg}	$-55 \sim 150$	$^\circ C$

* $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

●Packaging specifications

Type	Package	Bulk
	Code	—
	Basic ordering unit (pieces)	500
2SK2460N		○

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate leakage current	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$
Drain cutoff current	I_{DSS}	—	—	100	μA	$V_{DS} = 250\text{V}$, $V_{GS} = 0\text{V}$
Gate threshold voltage	$V_{GS(th)}$	2	—	4	V	$V_{DS} = 10\text{V}$, $I_D = 1\text{mA}$
Drain-source on-state resistance	$R_{DS(on)}$	—	0.55	0.75	Ω	$I_D = 2.5\text{A}$, $V_{GS} = 10\text{V}$
Forward propagation admittance	$ Y_{fs} $	2	3.5	—	S	$V_{DS} = 10\text{V}$, $I_D = 2.5\text{A}$
Input capacitance	C_{iss}	—	500	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	150	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	35	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	7	—	ns	$I_D = 2.5\text{A}$, $V_{DD} \approx 100\text{V}$
Rise time	t_r	—	15	—	ns	$V_{GS} = 10\text{V}$
Turn-off delay time	$t_{d(off)}$	—	30	—	ns	$R_L = 40\Omega$
Fall time	t_f	—	25	—	ns	$R_E = 10\Omega$
Reverse recovery time	t_{rr}	—	150	—	ns	$I_{DR} = 5\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery load	Q_{rr}	—	0.7	—	μC	$di/dt = 100\text{A}/\mu\text{s}$

● Electrical characteristic curves

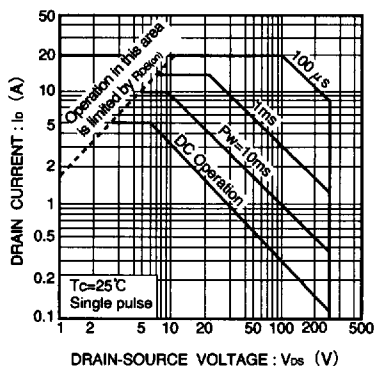


Fig.1 Maximum Safe Operating Area

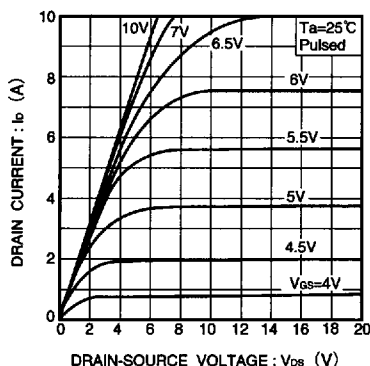


Fig.2 Typical Output Characteristics

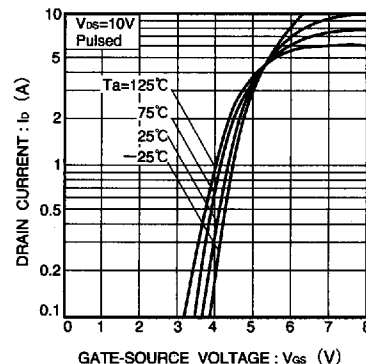


Fig.3 Typical Transfer Characteristics

7828999 0016781 248

● Electrical characteristic curves

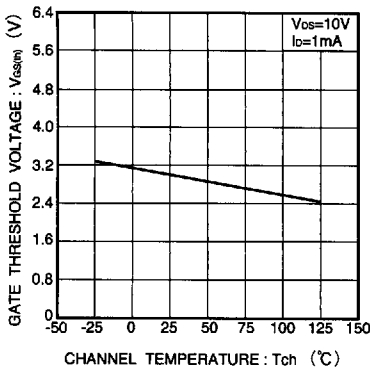


Fig.4 Gate Threshold Voltage vs. Channel Temperature

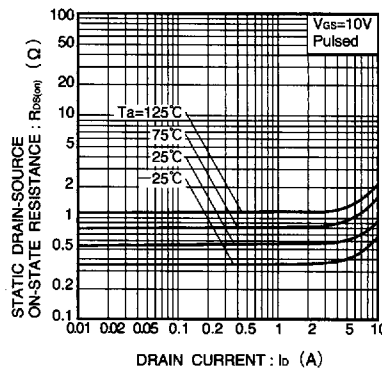


Fig.5 Static Drain-Source On-Resistance vs. Drain Current

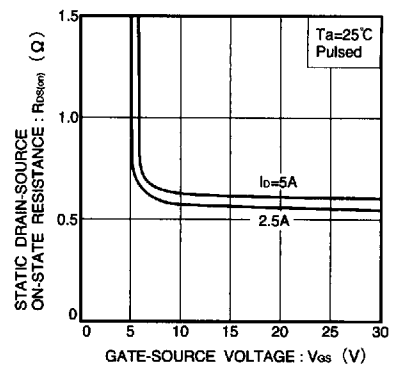


Fig.6 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

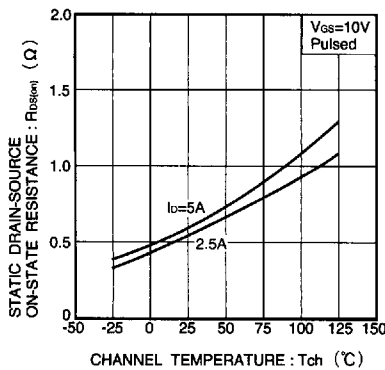


Fig.7 Static Drain-Source On-State Resistance vs. Channel Temperature

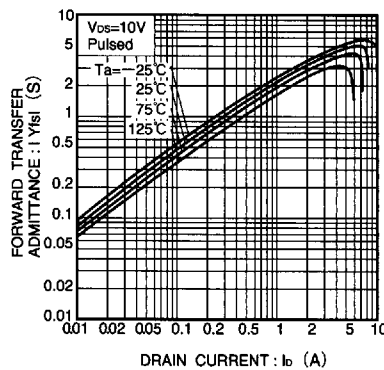


Fig.8 Forward Transfer Admittance vs. Drain Current

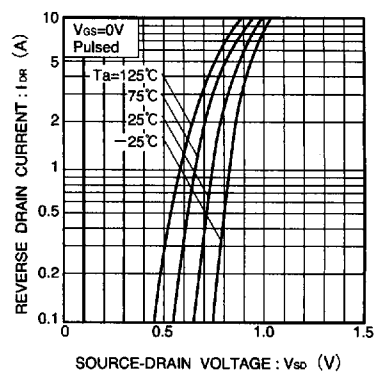


Fig.9 Reverse Drain Current vs. Source-Drain Voltage (I)

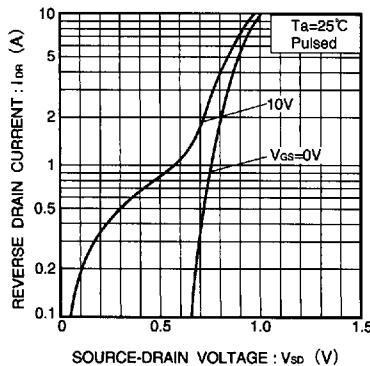


Fig.10 Reverse Drain Current vs. Source-Drain Voltage (II)

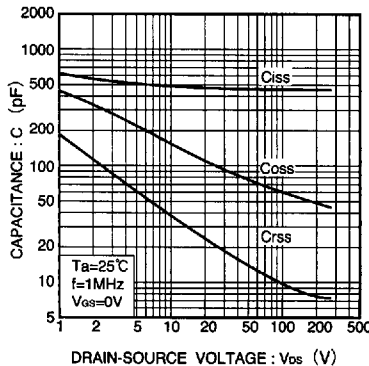


Fig.11 Typical Capacitance vs. Drain-Source Voltage

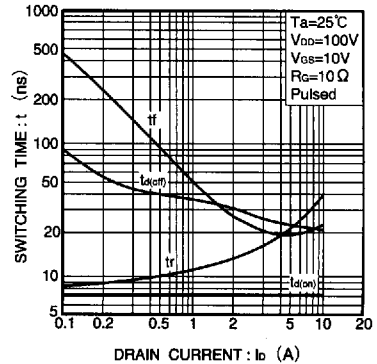


Fig.12 Switching Characteristics (See Figure. 16 and 17 for measurement circuits)

MOS FET

7828999 0016782 184

ROHM

● Electrical characteristic curves

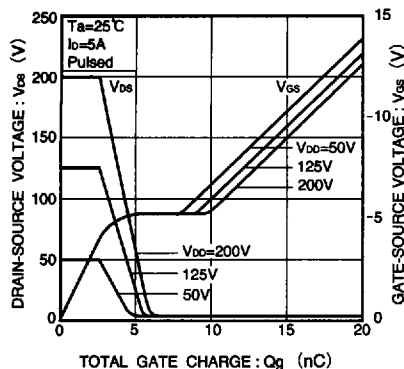


Fig.13 Dynamic Input Characteristics
(See Figure. 18 for measurement circuit)

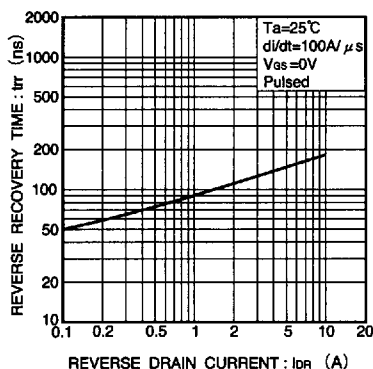


Fig.14 Reverse Recovery Time
vs. Reverse Drain Current

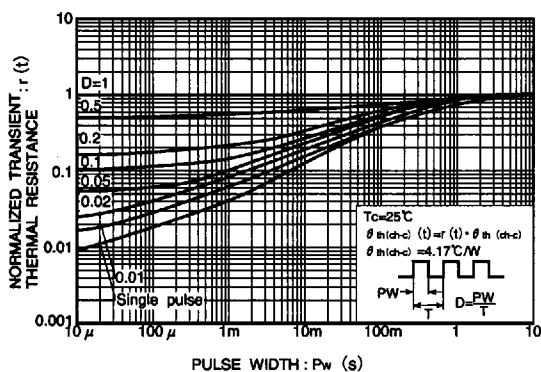


Fig.15 Normalized Transient Thermal
Resistance Vs. Pulse Width

● Switching characteristics measurement circuit

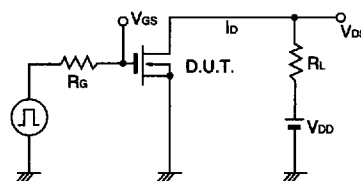


Fig.16 Switching Time Measurement Circuit

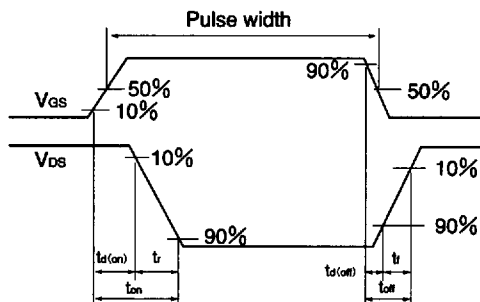


Fig.17 Switching Time Waveforms

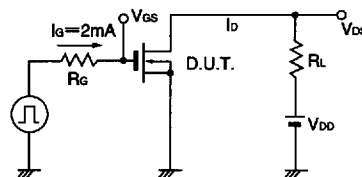
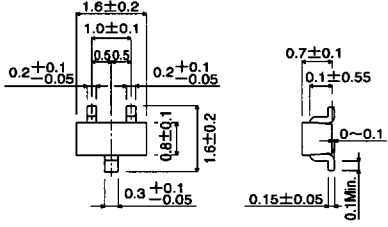
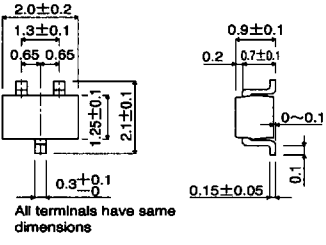
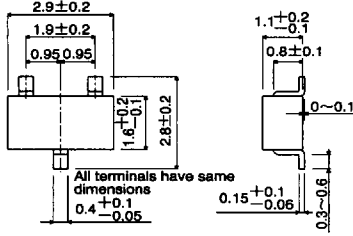
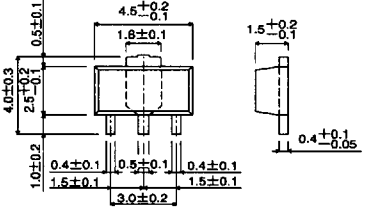


Fig.18 Gate Charge Measurement Circuit

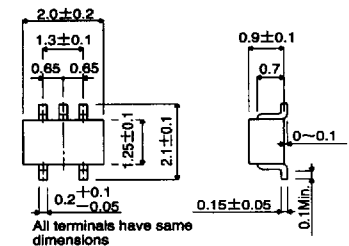
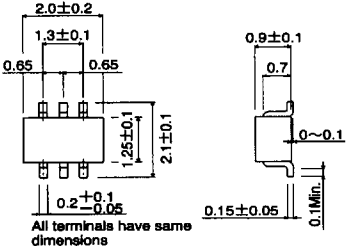
Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

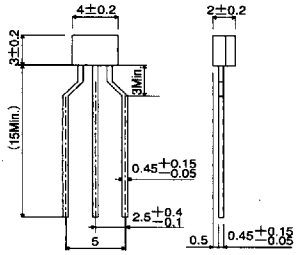
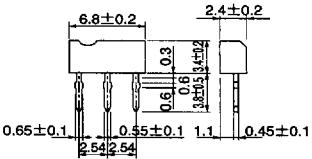
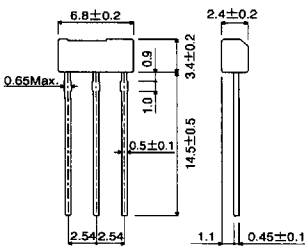
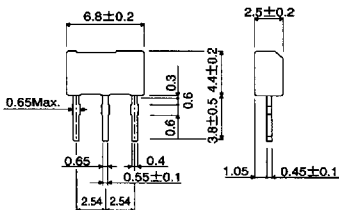
●Types and features of surface-mount packages

Type	External dimensions (Units : mm)	Features
EMT3 SC-75A type		<p>A more compact version of the UMT3 (SC-70), the EMT3 is the world's smallest transistor with a mold size of 1.6×0.8 mm. The mounting area is approximately 60% of the UMT3 and 30% of the SMT3, making it ideal for ultra-high density mounting. Mounting is possible with the same type of automatic mounting machine as the UMT3.</p>
UMT3 SC-70 type		<p>The UMT3 is a smaller version of the SMT3 (SC-59). The mounting area is approximately 60% of the SMT3, making it optimum for high density mounting. The taping size is the same as the SMT3, allowing use of conventional automatic mounting machines. Electrical characteristics and reliability are the same as the SMT3.</p>
SMT3 SC-59 type		<p>The SMT3 is a compact package suitable for small electronic devices and hybrid IC applications. With proven performance, this is one of the most basic small packages. With the exception of P_c (collector power dissipation), electrical characteristics are similar to leaded packages. Reliability is on the same level as the TO-92.</p>
MPT3 SC-62 type		<p>By itself the MPT3 has a P_c of 0.5 W ($T_a = 25^\circ\text{C}$), but when used on a $40 \times 40 \times 0.7$ mm ceramic board, $P_c = 2$ W ($T_c = 25^\circ\text{C}$), allowing high power to be obtained with a small package. The flat package makes it suitable for applications requiring compactness such as hybrid ICs. Available on tape for automatic mounting.</p>

Type	External dimensions (Units : mm)	Features
CPT 3 SC-63 type		<p>By itself the CPT3 has a P_c of 1 W ($T_a = 25^\circ\text{C}$), but a large P_c of several watts can be obtained with an appropriate mounting surface. At the same time the CPT3 is compact, making it suitable for high density mounting and hybrid ICs. Available on tape for automatic mounting.</p> <p>For vertical high density mounting, the leaded CPT (SC-64) type with the same mold size is also available.</p>
PSD3		<p>The PSD3 is a TO-220 class surface-mount package. A high P_c can be obtained with an appropriate mounting surface. Surface mounting allows a high vertical density, enabling the design of slim and compact devices. The PSD3 is available on tape for automatic mounting, and it helps improve mounting efficiency and reduce mounting cost.</p>
SMT5 SC-74A type		<p>The SMT5 consists of two connected transistors or digital transistors in an SMT3 (SC-59) package. The mounting area can be reduced by 50% compared to the SMT3 and the internal circuitry is complete, making this package ideal for high density mounting at half the assembly cost.</p>
SMT6 SC-74 type		<p>The SMT6 consists of two independent transistors or two independent digital transistors in an SMT3 (SC-59) package. The mounting area and mounting cost can be reduced by 50% compared to the SMT3, and the two transistors are independent to allow free configuration of a high density circuit.</p>

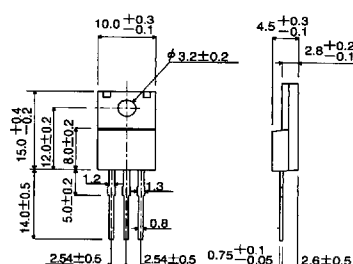
Type	External dimensions (Units : mm)	Features
UMT5 SC-88A type	 <p> 2.0 ± 0.2 1.3 ± 0.1 0.65 0.65 1.25 ± 0.1 2.1 ± 0.1 0.2 ± 0.1 0.15 ± 0.05 0.9 ± 0.1 0.7 $0 \sim 0.1$ 0.1 Min. </p> <p>All terminals have same dimensions</p>	<p>The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.</p>
UMT6 SC-88 type	 <p> 2.0 ± 0.2 1.3 ± 0.1 0.65 0.65 1.25 ± 0.1 2.1 ± 0.1 0.2 ± 0.1 0.15 ± 0.05 0.9 ± 0.1 0.7 $0 \sim 0.1$ 0.1 Min. </p> <p>All terminals have same dimensions</p>	<p>The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.</p>

●Types and features of leaded packages

Type	External dimensions (Units : mm)	Features
SPT (SC-72 type)	 <p>Diagram showing the external dimensions of the SPT (SC-72 type) package. The package is a small, rectangular component with a central body and two leads. Dimensions include: body width 4±0.2, body height 3±0.2, lead height 2±0.2, lead pitch 0.45±0.15, and lead width 0.45±0.15. A note indicates a minimum length of 15mm for the leads.</p>	<p>The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.</p>
FTR	 <p>Diagram showing the external dimensions of the FTR package. The package is a rectangular component with a central body and two leads. Dimensions include: body width 6.8±0.2, body height 0.3, lead height 2.4±0.2, lead pitch 0.65±0.1, and lead width 0.45±0.1. A note indicates a minimum length of 1.1mm for the leads.</p>	<p>SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.</p>
FTL	 <p>Diagram showing the external dimensions of the FTL package. The package is a rectangular component with a central body and two leads. Dimensions include: body width 6.8±0.2, body height 0.9, lead height 2.4±0.2, lead pitch 0.65Max, and lead width 0.45±0.1. A note indicates a minimum length of 1.1mm for the leads.</p>	<p>The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.</p>
ATR (SC-71 type)	 <p>Diagram showing the external dimensions of the ATR (SC-71 type) package. The package is a rectangular component with a central body and two leads. Dimensions include: body width 6.8±0.2, body height 0.3, lead height 2.5±0.2, lead pitch 0.65±0.1, and lead width 0.45±0.1. A note indicates a minimum length of 1.05mm for the leads.</p>	<p>SC-71type with a height of 4.4 mm and a P_c=1W type.</p>

EXPLANATION

Type	External dimensions (Units : mm)	Features
ATV		The ATV is a radial tapping version of the highly popular ATR. This enables automatic high-density mounting with a radial insertion machine.
TO-92 (SC-43 type)		The SC-43 is for general purpose small signals.
TO-126FP		The TO-126FP is an isolation type package based on a TO-126 full mold. In addition to the features of the TO-126, molded heat sink fins allow easy isolation of the heat sink.
TO-220FP (SC-67 type)		The TO-220FP is an isolation type package based on a TO-220 full mold. In addition to the features of the TO-126 and TO-220, molded heat sink fins allow easy isolation of the heat sink.

Type	External dimensions (Units : mm)	Features
TO-220FN	 <p>Technical drawing of the TO-220FN transistor package showing top and side views with dimensions in mm.</p> <p>Top View Dimensions:</p> <ul style="list-style-type: none"> Overall width: $10.0^{+0.3}_{-0.1}$ Overall height: $15.0^{+0.4}_{-0.2}$ Distance from top edge to mounting hole center: $12.0^{+0.2}_{-0.2}$ Distance from bottom edge to mounting hole center: $8.0^{+0.2}_{-0.2}$ Distance from left edge to mounting hole center: $5.0^{+0.2}_{-0.2}$ Mounting hole diameter: $\phi 3.2^{+0.2}_{-0.2}$ Distance between mounting holes: $2.54^{+0.5}_{-0.5}$ Distance from mounting hole to lead start: $0.75^{+0.1}_{-0.05}$ Lead thickness: 0.8 Lead width at base: $2.6^{+0.5}_{-0.5}$ <p>Side View Dimensions:</p> <ul style="list-style-type: none"> Overall height: $4.5^{+0.3}_{-0.1}$ Distance from base to mounting hole: $2.8^{+0.2}_{-0.1}$ 	<p>The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis.</p> <p>To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.</p>

EXPLANATION